# **MOTOROLA** SEMICONDUCTOR TECHNICAL DATA

## Microwave Pulse Power Transistor 150 Watts Peak NPN 1025-1150 MHz

Designed for 1025-1150 MHz pulse common base amplifiers.

- Guaranteed Performance at 1090 MHz
  - Output Power = 150 Watts Peak
  - Gain = 9.5 dB Min
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Characterized with 10 μs, 10% Duty Cycle Pulses
- · Silicon Nitride Passivated
- · Gold Metallized, Emitter Ballasted for Long Life
- · Internal Input and Output Matching
- · Hermetically Sealed Package

### MRF10150H\*



#### **AVAILABLE AS**

Case 376B-02

1) JANTX: MRF10150HX 2) JANTXV: **MRF10150HXV** 3) JANS: MRF10150HS 4) COML+: **MRF10150HC** 

PACKAGE:

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	65	Vdc
Collector-Base Voltage	VCBO	65	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.5	Vdc
Collector Current - Peak (1)	lc	14	Adc
Device Dissipation at T <sub>C</sub> = 25 °C (1 & 2) Derate above 25 °C	PD	700 4.0	W/ °C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 200	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	R <sub>0</sub> JC	0.25	°C/W

#### NOTES:

(continued)

- 1. Under pulse RF operating conditions.
- 2. These devices are designed for RF operation. The total device dissipation rating applies only when operated as RF amplifier.
- 3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

\*Motorola Preferred Device. Preferred devices are Motorola recommended choices for future use and best overall value. Teflon is a registered trademark of du Pont de Nemours & Co., Inc.



### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 60 mAdc, V <sub>BE</sub> = 0)	V <sub>(BR)</sub> CES	65	_	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 60 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	65	_	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	3.5	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 36 Vdc, I <sub>E</sub> = 0)	<sup>I</sup> CBO		25	mAdc

#### **ON CHARACTERISTICS**

DC Current Gain (IC = 5.0 Adc, VCE = 5.0 Vdc) her 20				 
1	DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	''FE	20	 _

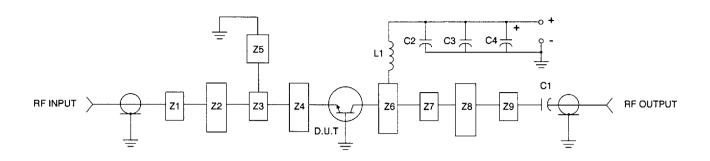
#### **FUNCTIONAL TESTS**

Common-Base Amplifier Power Gain (V <sub>CC</sub> = 50 Vdc, P <sub>OUT</sub> = 150 W Peak, f = 1090 MHz)	G <sub>PB</sub>	9.5	_	dB
Collector Efficiency (V <sub>CC</sub> = 50 Vdc, P <sub>OUT</sub> = 150 W Peak, f = 1090 MHz)	η	40	-	%
Load Mismatch (V <sub>CC</sub> = 50 Vdc, P <sub>OUT</sub> = 150 W Peak, f = 1090 MHZ)	Ψ	No Degra	dation in Out	out Power

#### ASSURANCE TESTING (Pre/Post Burn-In)

Burn-In Test Conditions:  $V_{CB} \ge 10$  Vdc,  $T_J = 162.5$  °C + 12.5 °C

Characteristic	Symbol	Min	Max	Unit
Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0)	СВО	_	25	mAdc
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	hFE	20	_	_



C1 - 82 pF 100 mil Chip Capacitor

C2 - 39 pF 100 mil Chip Capacitor

C3 – 0.1 μF

 $C4 - 100 \mu F$ , 100 Vdc, Electrolytic

L1 – 3 turns #18 AWG, 1/8" ID, 0.18 Long Z1-Z9 – Microstrip, see details below Board Material – 0.030" Glass Teflon® 2 Oz. Copper,  $\epsilon_{r}$  = 2.55

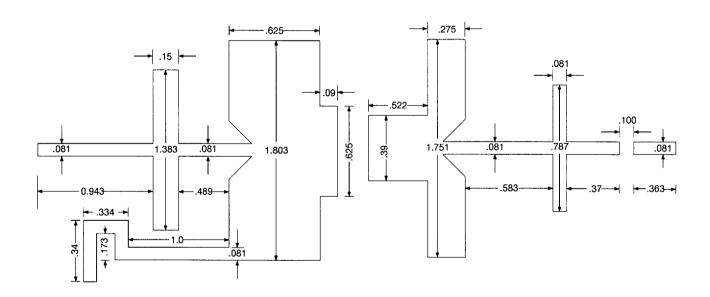


Figure 1. Test Circuit

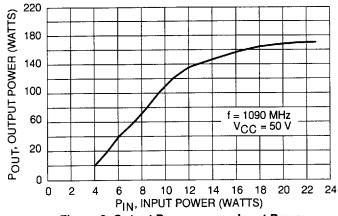
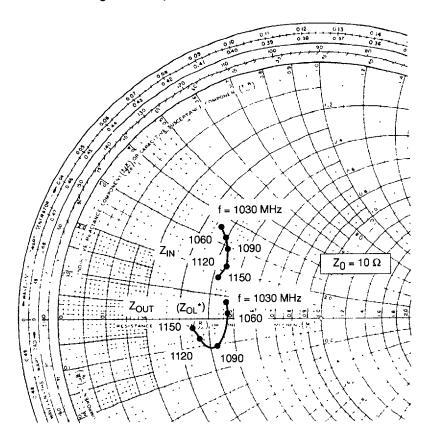


Figure 2. Output Power versus Input Power



 $P_{OUT}$  = 150 W Pk,  $V_{CC}$  = 50 V

f MHz	Z <sub>IN</sub> OHMS	Z <sub>OL</sub> * (Z <sub>OUT</sub> ) OHMS
1030	3.8 + j3.5	4.6 +j0.7
1060	4.0 + j3.3	4.6 + j0.3
1090	4.2 + j3.0	4.1 - j1.0
1120	4.4 + 2.3	3.8 - j0.8
1150	4.1 + j1.8	3.6 - j0.3

Z<sub>OL</sub>\* is the conjugate of the optimum load impedance into which the device operates at a given output power, voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

#### **TABLE 1. SCREENING REQUIREMENTS**

SCREEN	METHOD	нх	нху
Internal visual inspection (precap)	2072	N/A	100%
2. High temperature non-operating life	1032	100%	100%
3. Temperature cycling	1051	100%	100%
4. Constant Acceleration (Gold wires only)	2006	100%	100%
5. Hermetic seal (Fine and Gross)	1071	100%	100%
6. Establish Unit Identity	none	100%	100%
7. Interim electrical parameters	as specified	100%	100%
8. High temperature reverse bias (HTRB)	1039	100%	100%
9. Interim electrical parameters	as specified	100%	100%
10. Power burn-in	1039	100%	100%
11. Final electrical parameters	as specified	100%	100%
12. Hermetic seal (Fine and Gross)	1071	optional	optional

#### **GROUP A TEST SEQUENCE**

		Subgroups	
A1	A2	A3	A4
		Type of Test	
Visual/Mechanical Package: Dimensions, Marking	DC Tests V(BR)CBO V(BR)CES V(BR)EBO ICBO hFE	Hi/Lo Temp Not Applicable	AC Tests  GpB  η

#### **GROUP B TEST SEQUENCE**

		S	ubgroups		
B1**	B2*	B3*	B4	B5	B6*
		,	Type of Test		
Solderability (1)	Temp. Cycling	Steady State Operating Life	Decap Visual	Not Required	High Temp. Life (Non-Operating)
Resistance to	Hermetic Seal	-   -   -   -   -   -   -   -   -   -			(Non operating)
Solvents	Fine Gross	Bond Strength			

<sup>\*</sup> The tests in this subgroup are preceded and followed by I<sub>CBO</sub> and h<sub>FE</sub> electrical tests.

#### **GROUP C TEST SEQUENCE\***

		S	Subgroups		
C1	C2**	C3**	C4	C5	C6**
			Type of Test		
Physical Dimensions	Thermal Shock (Glass Strain) Terminal Strength Hermetic Seal Moist. Resistance	Mech. Shock  Vibration (Var. Freq.)  Const. Accel.	Salt Atmosphere	Not Applicable	Steady State Op Life

<sup>\*</sup> Group C is performed on the initial lot and requalification only.

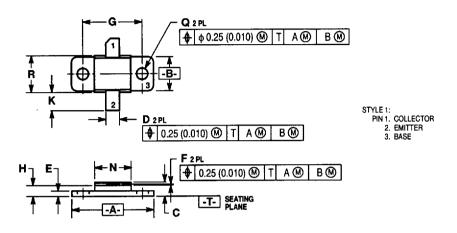
MRF10150H/D

<sup>\*\*</sup> Separate samples may be used for each test.

<sup>(1)</sup> Omit Steam Aging requirements.

<sup>\*\*</sup> The tests in this subgroup are preceded and followed by  $I_{\mbox{\footnotesize{CBO}}}$  and  $h_{\mbox{\footnotesize{FE}}}$  electrical tests.

#### **OUTLINE DIMENSIONS**



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- CONTROLLING DIMENSION: INCH.
- 3. 376B-01 OBSOLETE, NEW STANDARD 376B-02.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	22.61	23.11	0.890	0.910
В	9.40	10.16	0.370	0.400
C	3.69	4.06	0.145	0.160
D	3.56	4.06	0.140	0.160
E	1.40	1.65	0.055	0.065
F	0.08	0.15	0.003	0.006
G	16.51 BSC		0.65	BSC
Н	2.80	3.30	0.110	0.130
K	4.57	5.59.	0.180	0.220
N	9.91	10.41	0.390	0.410
Q	2.93	3.42	0.115	0.135
R	9.91	10.41	0.390	0.410

**CASE 376B-02** 

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